1. Record Nr. UNINA9910785549903321

Autore	Cutsinger James S. <1953->
Titolo	Advice to the serious seeker : meditations on the teaching of Frithjof Schuon / / James S. Cutsinger
Pubbl/distr/stampa	Albany : , : State University of New York Press, , 1997 ©1997
Descrizione fisica	1 online resource (x, 225 pages) : illustrations, portrait
Collana	SUNY series in Western esoteric traditions
Disciplina	200/.92
Soggetti	Spiritual life Religions Religion
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di bibliografia	Includes bibliographical references (p. 219-220) and index.
Nota di contenuto	""Advice to the Serious Seeker: Meditations on the Teaching of Frithjof Schuon ""; ""Contents ""; ""Preface ""; ""Introduction: Landmarks on the Road Ahead ""; ""Chapter 1: The Way of Knowledge ""; ""Chapter 2: Thinking the Unthinkable ""; ""Chapter 3: Proofs of God ""; ""Chapter 4: The Intellect ""; ""Chapter 5: Degrees of Reality ""; ""Chapter 6: The Doctrine of Illusion ""; ""Chapter 7: The Open Door ""; ""Chapter 8: Conforming to God ""; ""Chapter 9: Perfection and Anonymity ""; ""Chapter 10: Humility ""; ""Chapter 11: Charity ""; ""Chapter 12: Veracity "" ""Chapter 13: Predestination and Freedom """"; "Chapter 14: A Space before God ""; ""Chapter 15: The World as Symbol ""; ""Chapter 16: The Message of the Human Body ""; ""Chapter 17: Sacred Art ""; ""Chapter 18: The Practice of Beauty ""; ""Chapter 19: Movement toward God ""; ""Chapter 20: Faith ""; ""Chapter 21: Method and Grace ""; ""Chapter 22: Concentration through Intention ""; ""Chapter 23: Invocation of the Name ""; ""Chapter 24: Spiritual Direction ""; ""Chapter 25: Our Final Goal ""; ""Epilogue: Perennial Philosophy and Transcendent Unity ""; ""Sources of Quotations ""; ""Bibliography of Works by Frithjof Schuon ""; ""Suggested Reading ""; ""Index ""

2. Record Nr. UNINA9911003588303321

Autore	Baliga B. Jayant
Titolo	The BaSIC topology : a revolutionary power device control strategy / / B. Jayant Baliga, Ajit Kanale
Pubbl/distr/stampa	Cham : , : Springer, , [2025] ©2025
ISBN	9783031866302
Descrizione fisica	1 online resource (xxii, 316 pages) : illustrations
Disciplina	621.381044
Soggetti	Power semiconductors Electric power production Power electronics Electronic circuits Electronics Power Electronics Electronic Circuits and Systems Electronics and Microelectronics, Instrumentation Electrical Power Engineering
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Introduction -- Short-circuit withstand capability -- Conventional current sensing in devices -- The BaSIC topology concept -- Application of the BaSIC Topology to Si IGBTs -- Application of the BaSIC Topology to SiC Power MOSFETs -- Application of the BaSIC Topology to GaN HEMT devices -- Current Sensing using the BaSIC Topology -- Eliminating repetitive short-circuit failure using the BaSIC Topology -- Avalanche ruggedness of the BaSIC Topology to GaN HEMT devices -- Optimization of Silicon Depletion-Mode MOSFETs for the BaSIC Topology -- Selection Methodology for Silicon Enhancement-Mode MOSFETs for the BaSIC Topology -- Comparison of the BaSIC Topology to the conventional DESAT topology -- Synopsys.
Sommario/riassunto	The BaSIC topology is a revolutionary method for controlling power semiconductor devices. It enables monitoring the current flow through

the devices while providing a unique current limiting capability that enhances their short-circuit withstand capability. The book describes the BaSIC topology concept and contrasts it with previous approaches. It provides an extensive description of the application of the BaSIC topology to silicon IGBTs, silicon carbide power MOSFETs, and GaN HEMT devices. The ability to extend the short-circuit withstand time to over 10 ms for SiC power MOSFETs has been achieved for the first time with the BaSIC topology. The BaSIC topology is the only approach shown to eliminate the failure of these devices under repetitive short-circuit events. The sensing of current in paralleled devices is demonstrated, eliminating the need for external sensors. The BaSIC topology has utility for various power electronics applications, including electric vehicles and industrial motor drives. Introduces the BaSIC topology – a revolutionary new approach for the control of power devices; Describes the application of the BaSIC topology to silicon IGBTs, silicon carbide power MOSFETs, and GaN HEMT devices; Written by the inventor of the insulated-gate bipolar transistor (IGBT) and the BaSIC topology concept.